

Fig. 1 - Typical IGBT Output Characteristics, $V_{GE} = 15\text{ V}$

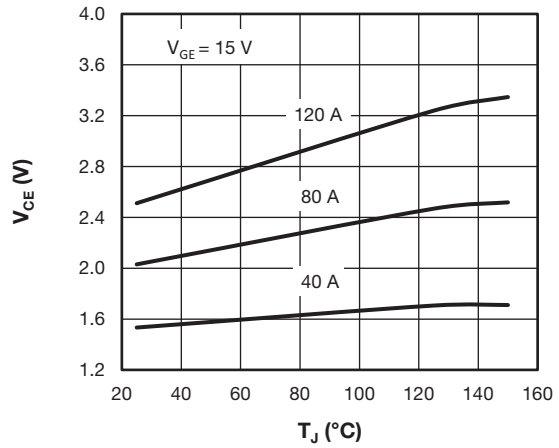


Fig. 4 - Collector to Emitter Voltage vs. Junction Temperature

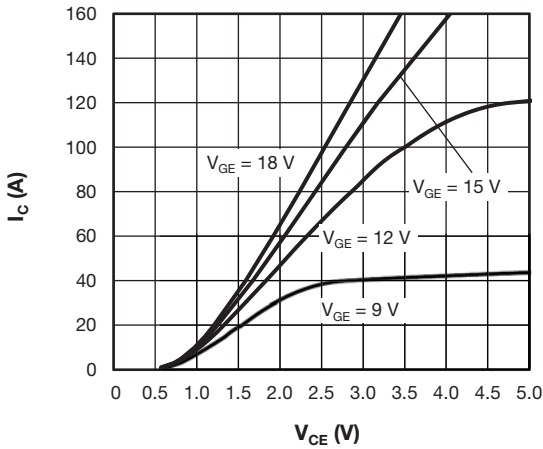


Fig. 2 - Typical IGBT Output Characteristics, $T_J = 125\text{ °C}$

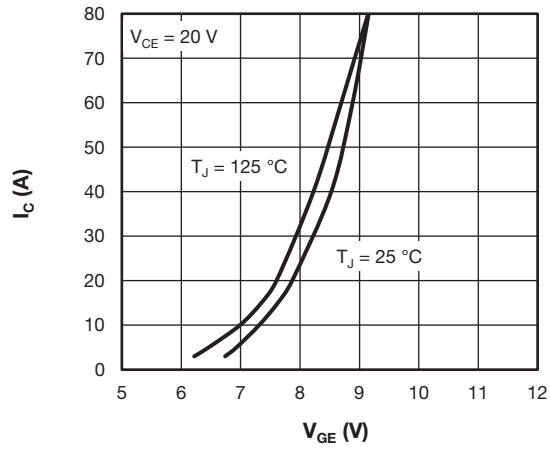


Fig. 5 - Typical IGBT Transfer Characteristics

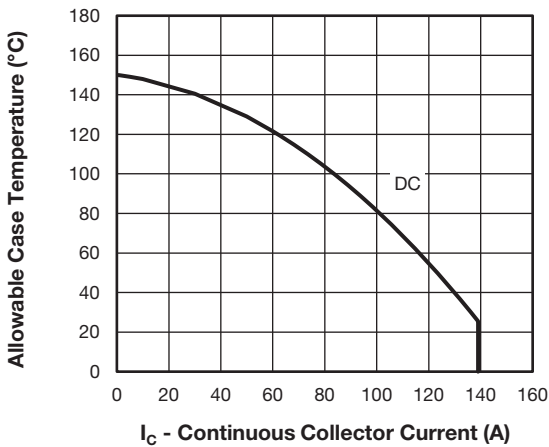


Fig. 3 - Maximum IGBT Continuous Collector Current vs. Case Temperature

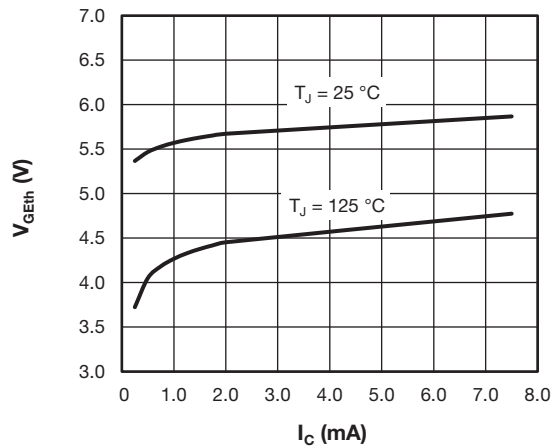


Fig. 6 - Typical IGBT Gate Threshold Voltage

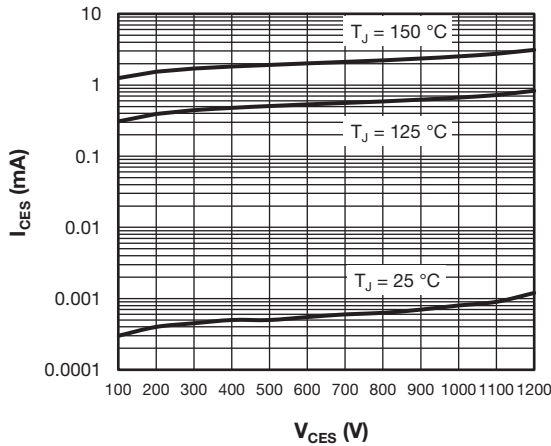


Fig. 7 - Typical IGBT Zero Gate Voltage Collector Current

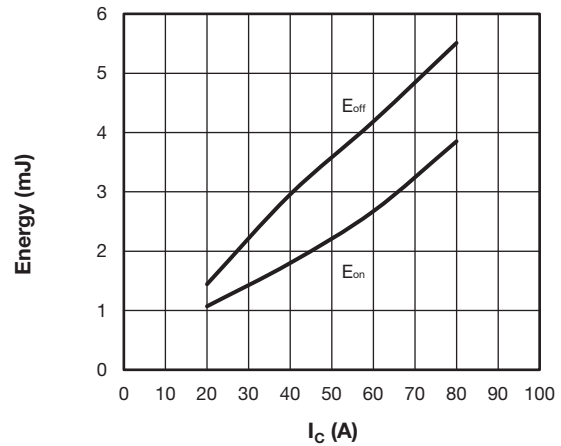


Fig. 10 - Typical IGBT Energy Loss vs I_C
 $T_J = 125\text{ °C}$, $V_{CC} = 600\text{ V}$, $R_g = 1.0\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

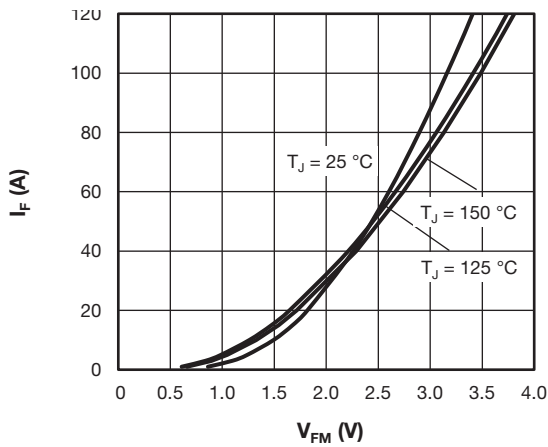


Fig. 8 - Typical Diode Forward Characteristics

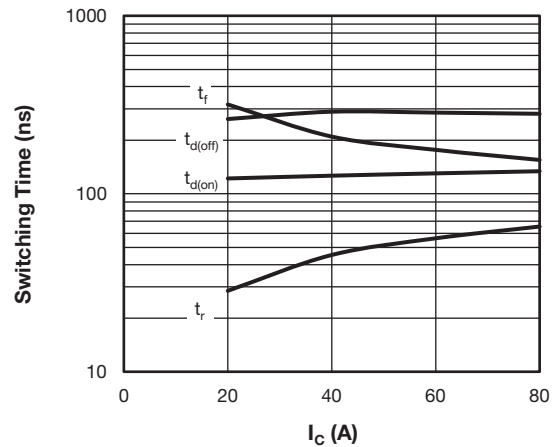


Fig. 11 - Typical IGBT Switching Time vs. I_C
 $T_J = 125\text{ °C}$, $V_{CC} = 600\text{ V}$, $R_g = 1.0\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

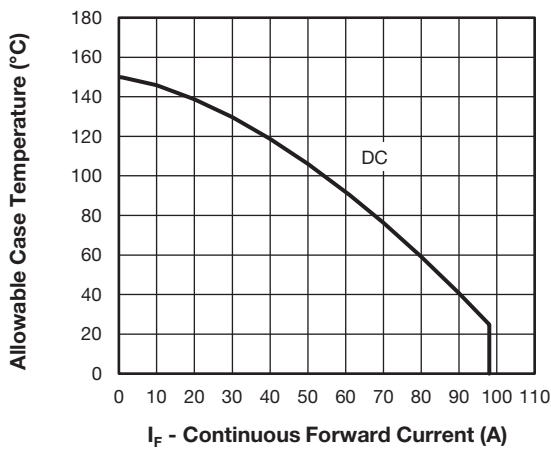


Fig. 9 - Maximum Diode Continuous Forward Current vs. Case Temperature

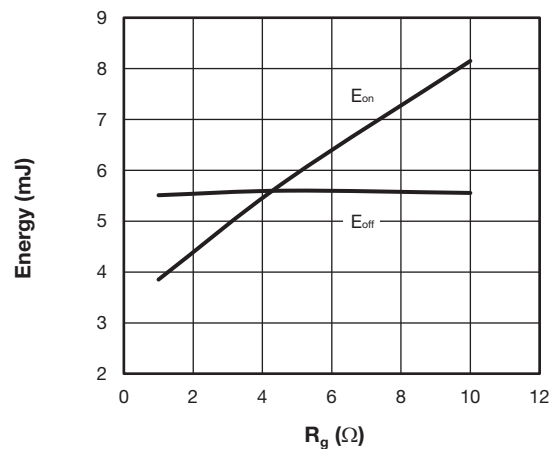


Fig. 12 - Typical IGBT Energy Loss vs. R_g
 $T_J = 125\text{ °C}$, $V_{CC} = 600\text{ V}$, $I_C = 80\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$